



## Low Voltage, 1-Ω Single SPDT Analog Switch (1:2 Multiplexer) with Power Down Protection

#### **DESCRIPTION**

The DG4157 is a high performance single pole double throw analog switch designed for 1.8 V to 5.5 V operation with single power rail.

Fabricated with high density CMOS technology, the device achieves low on resistance as 1  $\Omega$  at 4.5 V power supply and fast switching speed. The - 3 dB bandwidth is typically 117 MHz.

The DG4157 features break before make switch performance, and guarantees logic HIGH control input threshold as low as 1.4 V over the range up to 5.5 V.

It can handle both analog and digital signals and permits signals with amplitudes of up to  $V_{CC}$  to be transmitted in either direction.

Power down protection circuit is built in to prevent abnormal current path through signal pins during power down condition.

Each output pin  $(A, B_0, \text{ or } B_1)$  can withstand greater than 8 kV (human body model).

It is available in both SC-70-6 and miniQFN6 packages.

The features make it an ideal part for the switching of audio, video, and data stream.

#### **FEATURES**

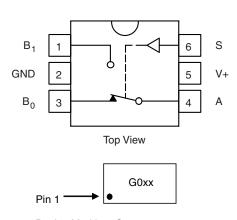
- Direct cross of industry standard xxx4157
- 1.8 V to 5.5 V operation voltage range
- Guaranteed 1.4 V logic high input threshold at V<sub>CC</sub> = 5.5 V
- 117 MHz, 3 dB bandwidth
- · Low on-resistance
- · Power down protection





#### **FUNCTIONAL BLOCK DIAGRAM AND PIN CONFIGURATION**

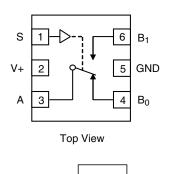
SC-70-6L



Device Marking: G0xx xx = Date/Lot Traceability Code

TRUTH TABLE	
Logic Input (S)	Function
0	B <sub>0</sub> Connected to A
1	B <sub>1</sub> Connected to A

### miniQFN-6L





x = Date/Lot Traceability Code

ORDERING INFORMATION				
Temp. Range	Package	Part Number		
- 40 °C to 85 °C	SC-70-6L	DG4157DL-T1-E3		
	miniQFN-6L	DG4157DN-T1-E4		

<sup>\*</sup> Pb containing terminations are not RoHS compliant, exemptions may apply.



ABSOLUTE MAXIMUM RATINGS					
Parameter		Limit	Unit		
Reference V+ to GND		- 0.3 to + 6	V		
S, A, B <sup>a</sup>		- 0.3 to (V+ + 0.3)	\ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \ \		
Continuous Current (Any terminal)		± 200	mA		
Peak Current (Pulsed at 1 ms, 10 % duty cycle)		± 400			
Storage Temperature	D Suffix	- 65 to 150	°C		
Power Dissipation (Packages) <sup>b</sup>	SC-70-6L <sup>c</sup>	250	mW		
	miniQFN-6L <sup>d</sup>	160	IIIVV		

#### Notes:

- a. Signals on A, or B or S exceeding V+ will be clamped by internal diodes. Limit forward diode current to maximum current ratings.
- b. All leads welded or soldered to PC board.
- c. Derate 3.1 mW/°C above 70 °C.
- d. Derate 2.0 mW/°C above 70 °C.

SPECIFICATIONS							
		Test Conditions Unless Otherwise Specified		Limits - 40 °C to 85 °C			
Parameter	Symbol	$V+ = 3.0 V, V_{IN} = 0 V or V+^{e}$	Temp.a	Min. <sup>b</sup>	Typ. <sup>c</sup>	Max. <sup>b</sup>	Unit
DC Characteristics							
		$V_{+} = 2.7 \text{ V}, B_{0} \text{ or } B_{1} = 1.5 \text{ V}, I_{0} = 100 \text{ mA}$	Room		1.7	2.5	
On Resistance	R <sub>ON</sub>	V1 = 2.7 V, B() of B1 = 1.0 V, I() = 100 III/V	Full			3	
Officessiance	1 ON	$V+ = 4.5 \text{ V}, B_0 \text{ or } B_1 = 3.5 \text{ V}, I_0 = 100 \text{ mA}$	Room		0.95	1.2	
		, 0 1 , 5	Full			1.4	
	D	$V+ = 2.7 \text{ V}, B_0 \text{ or } B_1 = 0.75 \text{ V}, 1.5 \text{ V},$ $I_0 = 100 \text{ mA}$	Room		0.2		Ω
On Resistance Flatness	R <sub>FLATNESS</sub>	$V+ = 4.5 \text{ V}, B_0 \text{ or } B_1 = 1 \text{ V}, 3.5 \text{ V},$	Room		0.14	0.3	
		$I_0 = 100 \text{ mA}$	Full			0.4	1
On Resistance Match	ΔR <sub>ON</sub>	$V+ = 2.7 \text{ V}, B_0 \text{ or } B_1 = 1.5 \text{ V},$ $I_0 = 100 \text{ mA}$	Room		0.04		
		$V+ = 4.5 \text{ V}, B_0 \text{ or } B_1 = 3.5 \text{ V},$	Room		0.05	0.12	1
		$I_{O} = 100 \text{ mA}$	Full			0.15	1
Switch OFF Lookaga Current	I <sub>OFF</sub>	V+ = 5.5 V, A = 1 V, 4.5 V B <sub>0</sub> or B <sub>1</sub> = 4.5 V, 1 V or Floating	Room	- 2		2	
Switch OFF Leakage Current			Full	- 20		20	nA
Switch ON Leakage Current	I <sub>ON</sub>		Room	- 4		4	
Switch ON Leakage Current	'ON		Full	- 40		40	
Digital Control							
Input, High Voltage	$V_{INH}$	V+ = 2.7 V to 5.5 V	Full	1.4			V
Input, Low Voltage	V <sub>INL</sub>	V+ = 2.7 V to 5.5 V	Full			0.4	7 °
Input Current	I <sub>INH</sub> , I <sub>INL</sub>	$V_{IN} = 0 \text{ or } V+$	Full	- 1		1	μΑ
Power Supply			•				
Power Supply Range	V+		Full	1.8		5.5	V
Quiescent Supply Current	I+	V+ = 5.5 V, V <sub>IN</sub> = 0 V, 5.5 V	Room		0.05	0.5	μΑ
			Full			1	



SPECIFICATIONS							
		Test Conditions Unless Otherwise Specified		Limits - 40 °C to 85 °C			
Parameter	Symbol	$V+ = 3.0 \text{ V}, V_{IN} = 0 \text{ V or } V+^{e}$	Temp.a	Min.b	Typ. <sup>c</sup>	Max.b	Unit
AC Characteristics							
		$V+ = 2.7 \text{ V}, B_0 \text{ or } B_1 = 1.5 \text{ V}, R_L = 50 \Omega,$	Room		40	55	
Turn-On Time <sup>d</sup>	t <sub>ON</sub>	$C_L = 35 pF$	Full			60	
turn-On Time	ON	$V+ = 4.5 \text{ V}, B_0 \text{ or } B_1 = 1.5 \text{ V}, R_L = 50 \Omega,$	Room		22	37	ns
		$C_L = 35 pF$	Full			40	
		V+ = 2.7 V, $B_0$ or $B_1$ = 1.5 V, $R_L$ = 50 Ω,	Room		12	27	
Turn-Off Time <sup>d</sup>	t <sub>OFF</sub>	$C_L = 35 pF$	Full			30	
iurn-Off Time*	OFF	$V+ = 4.5 \text{ V}, B_0 \text{ or } B_1 = 1.5 \text{ V}, R_L = 50 \Omega,$	Room		8	23	
		$C_L = 35 pF$	Full			25	
Break-Before-Make Time <sup>d</sup>		V+ = 2.7 V, B <sub>0</sub> = B <sub>1</sub> = 1.5 V, R <sub>L</sub> = 50 Ω, $C_L$ = 35 pF	- Room -	1	26		
	t <sub>BBM</sub>	V+ = 4.5 V, B <sub>0</sub> = B <sub>1</sub> = 1.5 V, R <sub>L</sub> = 50 Ω, $C_L$ = 35 pF		1	15		
Charge Injection <sup>d</sup>	Q	$C_L = 1 \text{ nF, } R_{GEN} = 0 \Omega, V_{GEN} = 0 \text{ V}$	Room		50		рC
d	OIDD	$R_L = 50 \Omega$ , $f = 1 MHz$	_		- 58		
Off Isolation <sup>d</sup>	OIRR	$R_L = 50 \Omega$ , $f = 10 MHz$	Room		- 31		- dB
Crosstalk <sup>d</sup>	V	$R_L$ = 50 $\Omega$ , $C_L$ = 5 pF, f = 1 MHz	Room		- 63		
	X <sub>TALK</sub>	$R_L$ = 50 Ω, $C_L$ = 5 pF, f = 10 MHz			- 36		
Bandwidth <sup>d</sup>	BW	R <sub>L</sub> = 50 Ω	Room		117		MHz
Total Harmonic Distortion <sup>d</sup>	THD	$R_L$ = 600 $\Omega$ , $V_{IN}$ = 0.5 V, f = 20 to 20 kHz	Room		0.02		%
Capacitance	1						
BX Port Off Capacitance <sup>d</sup>	C <sub>B(OFF)</sub>				20		
A Port On Capacitance <sup>d</sup>	C <sub>A(ON)</sub>	$R_L$ = 50 $\Omega$ , $C_L$ = 5 pF, f = 1 MHz	Room		57		pF
Control Pin Capacitance <sup>d</sup>	C <sub>IN</sub>	1			5		

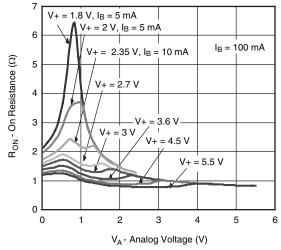
#### Notes

- a. Room = 25  $^{\circ}$ C, Full = as determined by the operating suffix.
- b. The algebraic convention whereby the most negative value is a minimum and the most positive a maximum, is used in this data sheet.
- c. Typical values are for design aid only, not guaranteed nor subject to production testing.
- d. Guarantee by design, nor subjected to production test.
- e. V<sub>IN</sub> = input voltage to perform proper function.

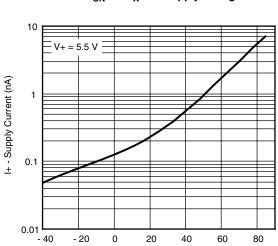
Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

# VISHAY

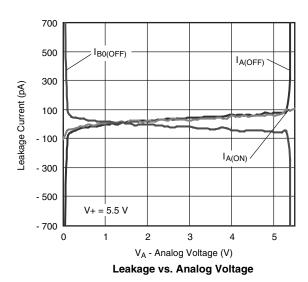
## **TYPICAL CHARACTERISTICS** $T_A = 25$ °C, unless otherwise noted

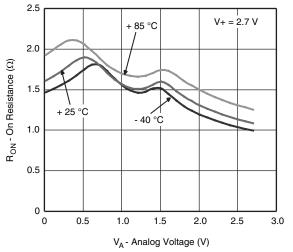


 $R_{ON}$  vs.  $V_A$  and Supply Voltage

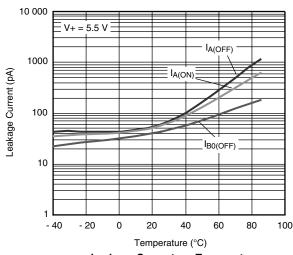


Temperature (°C)
Supply Current vs. Temperature

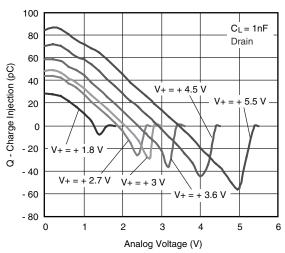




 $R_{\mbox{\scriptsize ON}}$  vs.  $V_{\mbox{\scriptsize D}}$  and Temperature



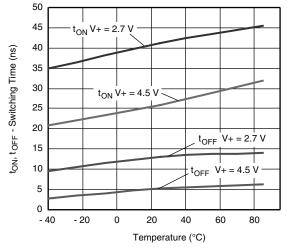
Leakage Current vs. Temperature



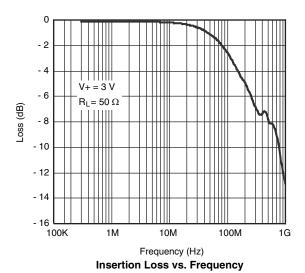
**CECA Charge Injection vs. Analog Voltage** 

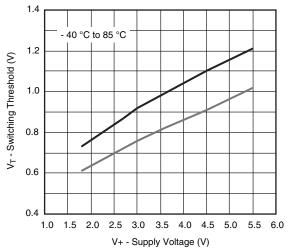


## **TYPICAL CHARACTERISTICS** $T_A = 25~^{\circ}C$ , unless otherwise noted

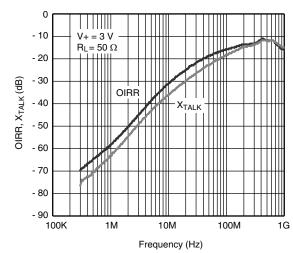


Switching Time vs. Temperature





Switching Threshold vs. Supply Voltage



Off-Isolation and Crosstalk vs. Frequency

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#### **TEST CIRCUITS**

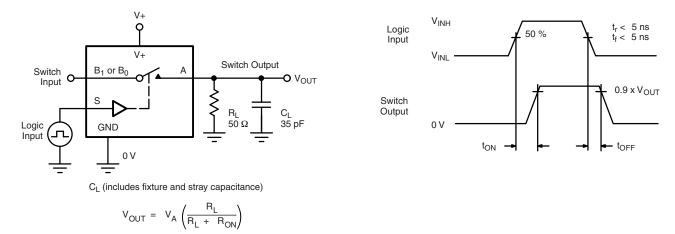


Figure 1. Switching Time

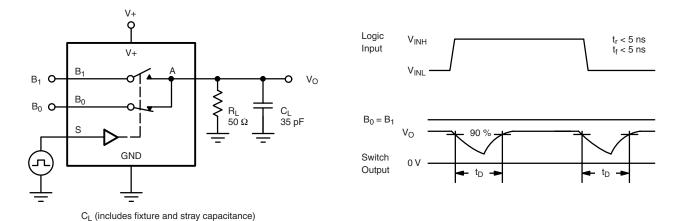


Figure 2. Break-Before-Make Interval

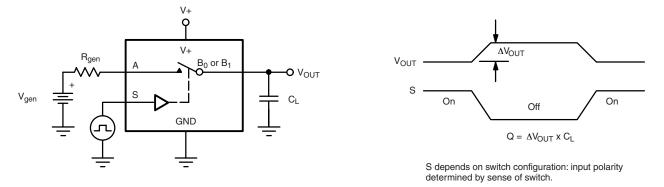


Figure 3. Charge Injection



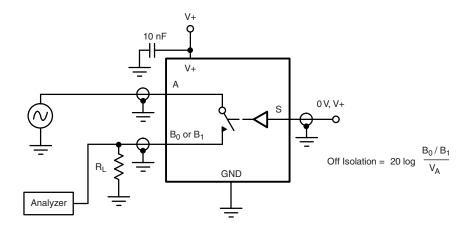


Figure 4. Off-Isolation

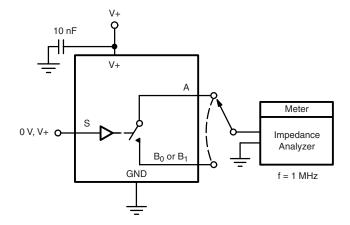


Figure 5. Channel Off/On Capacitance

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Revision: 18-Jul-08

Document Number: 91000 www.vishay.com